

Power MOSFET

200 mAmps, 50V N-Channel

•FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- Low threshold voltage ($V_{GS(th)}$: 0.5V... 1.5V) makes it ideal for low voltage applications.
- ESD Protected:2000V

• MARKING :J2

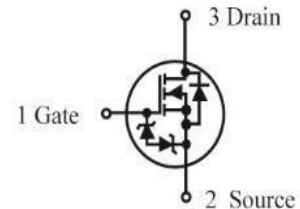
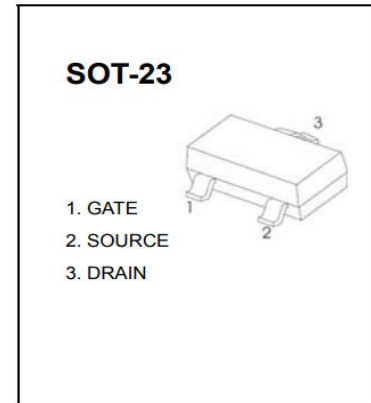
•MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	VDSS	50	V
Gate-to-Source Voltage –Continuous	VGS	± 20	V
Drain Current			mA
– Continuous $T_A = 25^\circ\text{C}$	ID	200	
– Pulsed ($t_p \leq 10\mu\text{s}$)	IDM	800	

•THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation, FR-4 Board (Note 1) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	PD	150	mW
Thermal Resistance, Junction-to-Ambient(Note 1)	R θ JA	833	$^\circ\text{C}/\text{W}$
Junction and Storage temperature	TJ, Tstg	$-55 \sim +150$	$^\circ\text{C}$
Maximum Lead Temperature for Solde Purposes, for 10 seconds	TL	260	$^\circ\text{C}$

1. FR-4 = 1.0×0.75×0.062 in.



•ELECTRICAL CHARACTERISTICS (Ta= 25°C)

OFF CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Drain–Source Breakdown Voltage (VGS = 0, ID = 250μA)	VBRDSS	50	-	-	V
Zero Gate Voltage Drain Current (VGS = 0, VDS = 25 V) (VGS = 0, VDS = 50 V)	IDSS	-	-	0.1 0.5	μA
Gate–Body Leakage Current, Forward (VGS = 20 V)	IGSSF	-	-	10	μA
Gate–Body Leakage Current, Reverse (VGS = - 20 V)	IGSSR	-	-	-10	μA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage (VDS = VGS, ID = 1.0mA)	VGS(th)	0.5	-	1.5	V
Static Drain–Source On–State Resistance (VGS = 2.75 V, ID < 200 mA, TA = -40°C to +85°C) (VGS = 5.0 V, ID = 200 mA)	RDS(on)	-	5.6	10 3.5	Ohms
Forward Transconductance (VDS = 25 V, ID = 200 mA, f = 1.0 MHz)	gfs	100	-	-	mS

DYNAMIC CHARACTERISTICS

Input Capacitance (VDS = 25 V, VGS = 0, f = 1.0 MHz)	Ciss	-	22.8	-	pF
Output Capacitance (VDS = 25 V, VGS = 0, f = 1.0 MHz)	Coss	-	3.5	-	pF
Reverse Transfer Capacitance (VDS = 25 V, VGS = 0, f = 1.0 MHz)	Crss	-	2.9	-	pF

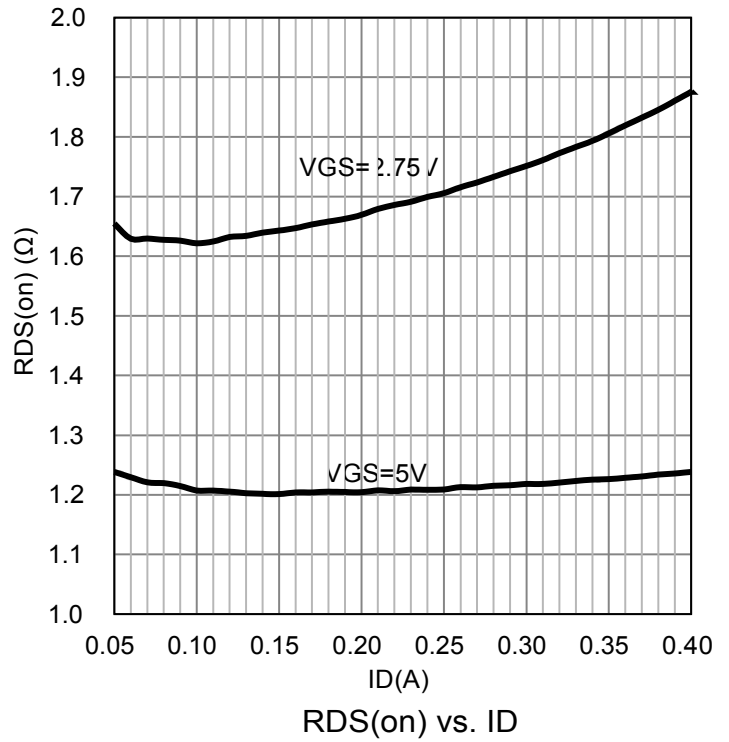
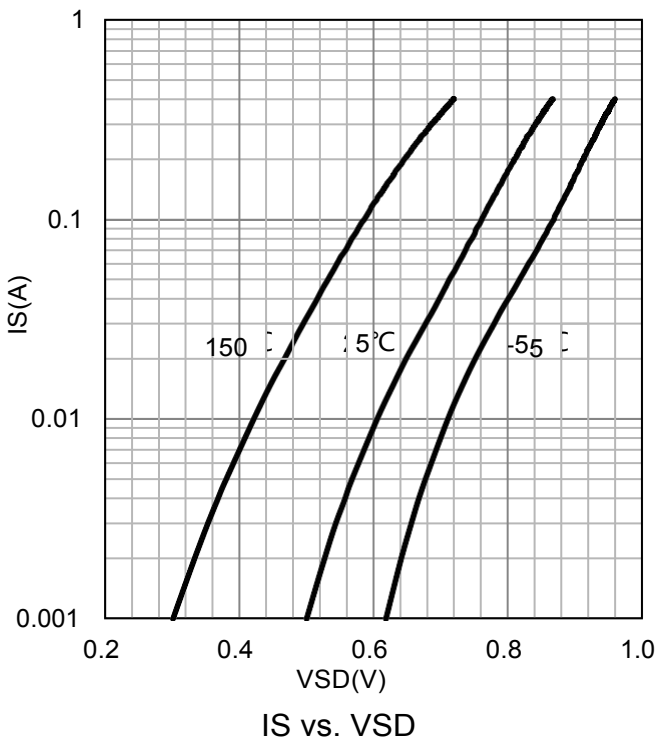
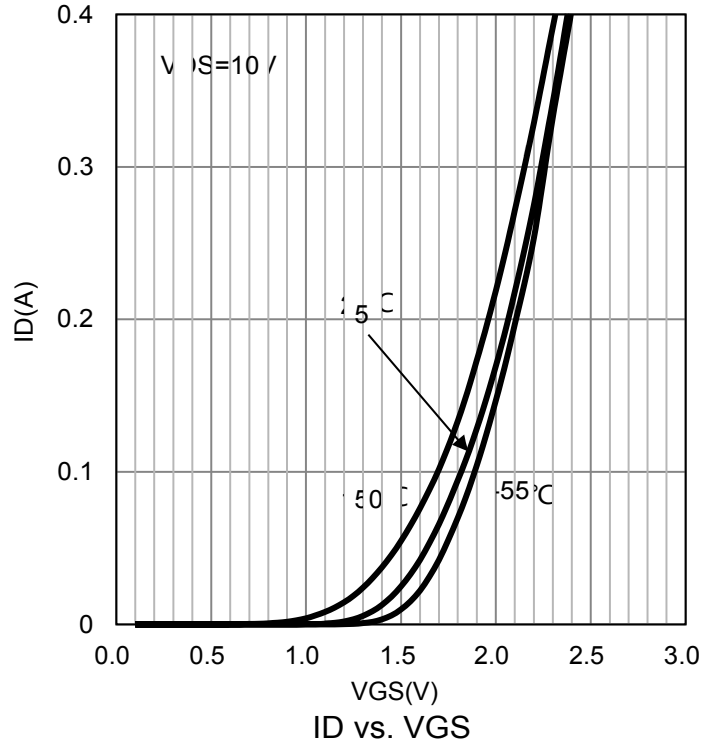
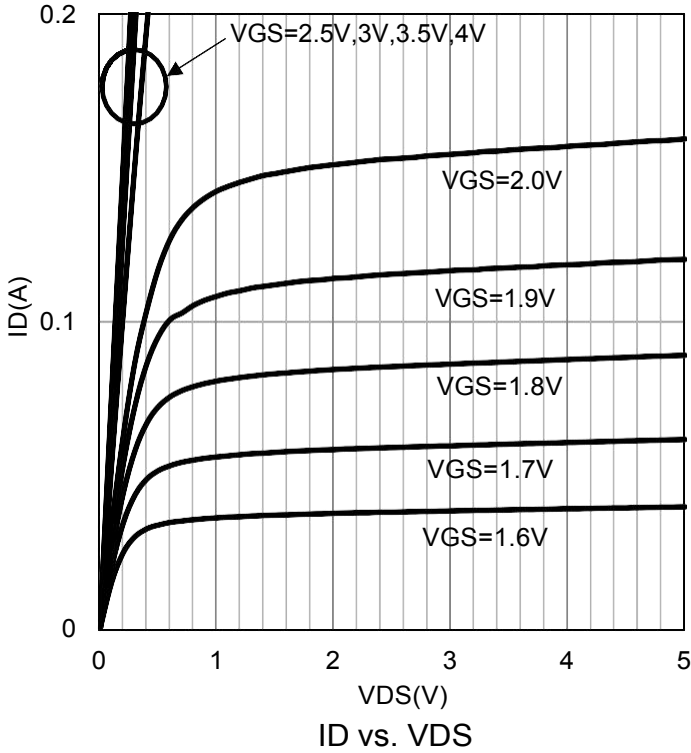
SWITCHING CHARACTERISTICS

Turn-On Delay Time	(VDD = 30 V , VGEN = 10 V, RG =25Ω ,RL =60 Ω, ID =500 mA)	td(on)	-	3.8	-	ns
Turn-Off Delay Time		td(off)	-	19	-	

2.Pulse Test: Pulse Width ≤300 μs, Duty Cycle ≤2.0%.

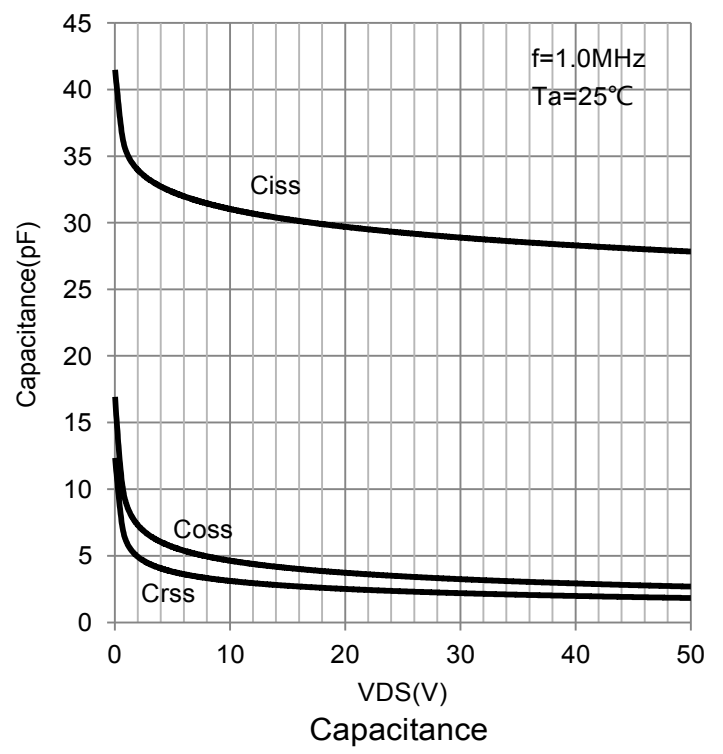
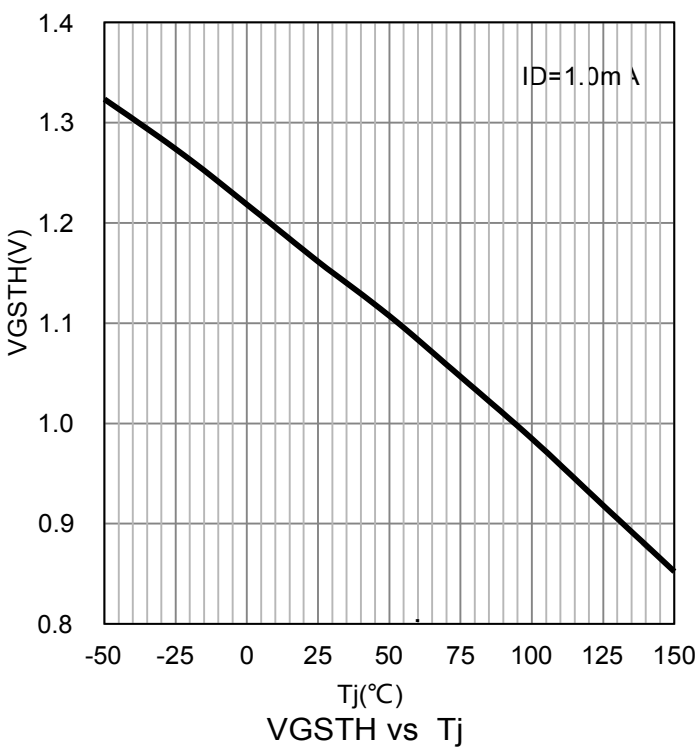
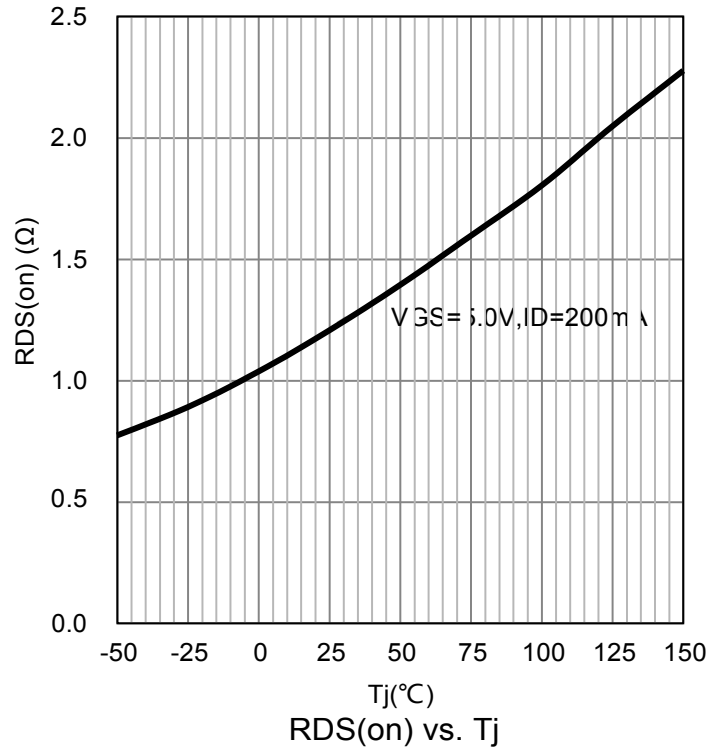
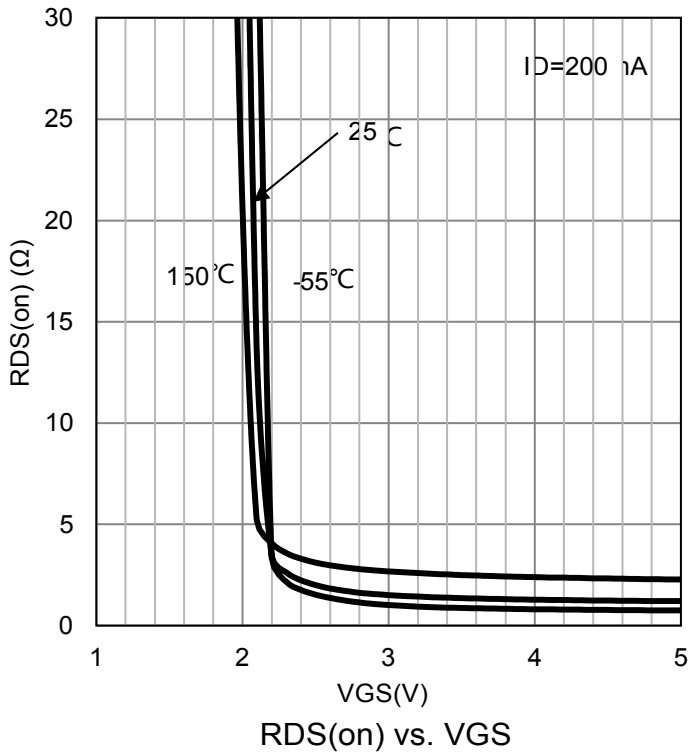


•ELECTRICAL CHARACTERISTICS CURVES





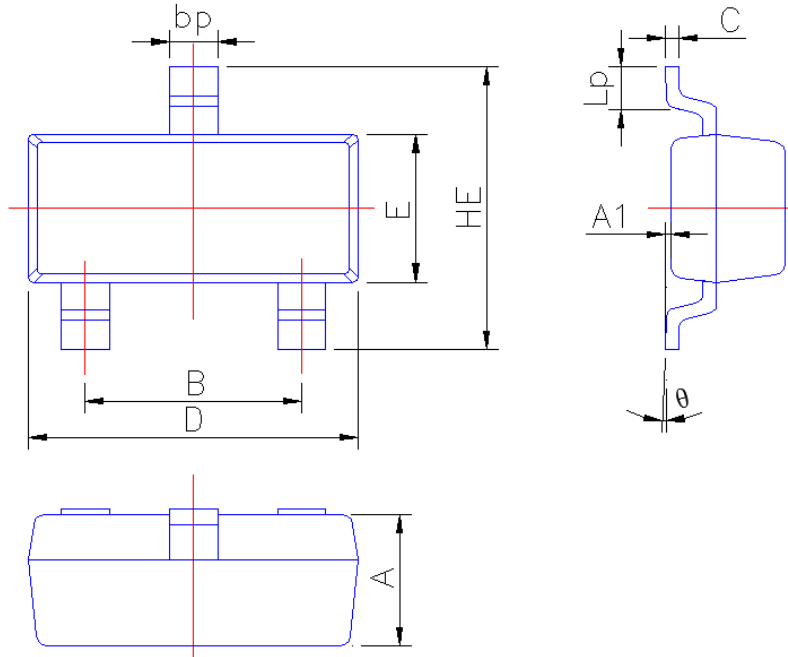
•ELECTRICAL CHARACTERISTICS CURVES(Con.)



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.10
A1	0.013	0.100
B	1.80	2.00
bp	0.35	0.50
C	0.09	0.150
D	2.80	3.00
E	1.20	1.40
HE	2.20	2.80
Lp	0.20	0.50
θ	0°	5°